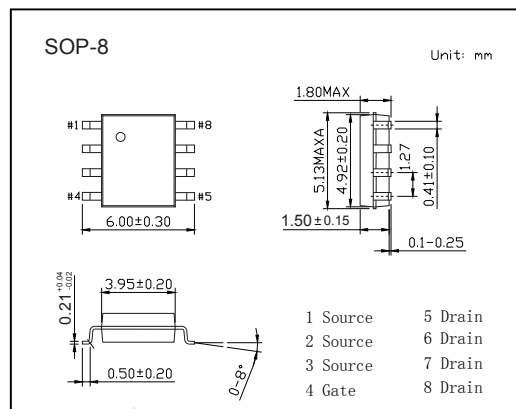
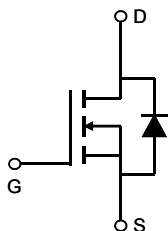


N-Channel MOSFET

AO4312 (KO4312)

■ Features

- $V_{DS} (V) = 36V$
- $I_D = 23 A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 4.5m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 6.2m\Omega$ ($V_{GS} = 4.5V$)

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	36	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	23	A
		18	
Pulsed Drain Current	I_{DM}	264	
Avalanche Current	I_{AS}, I_{AR}	45	mJ
Avalanche energy	$L=0.1mH$	101	
Power Dissipation	P_D	4.2	W
		2.7	
Thermal Resistance.Junction- to-Ambient	R_{thJA}	30	$^\circ C/W$
		60	
Thermal Resistance.Junction- to-Lead	R_{thJL}	15	$^\circ C$
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 to 150	

N-Channel MOSFET

AO4312 (KO4312)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 uA, V _{GS} =0V	36			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =36V, V _{GS} =0V			1	uA
		V _{DS} =36V, V _{GS} =0V, T _J =55°C			5	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.3		2.3	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A			4.5	mΩ
		V _{GS} =10V, I _D =20A T _J =125°C			6.9	
		V _{GS} =4.5V, I _D =20A			6.2	
On State Drain Current	I _{D(ON)}	V _{GS} =10V, V _{DS} =5V	264			A
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =20A		110		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =18V, f=1MHz	1560		2345	pF
Output Capacitance	C _{oss}		475		890	
Reverse Transfer Capacitance	C _{rss}		14		85	
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.5		1.6	Ω
Total Gate Charge (10V)	Q _g	V _{GS} =10V, V _{DS} =18V, I _D =20A	22		34	nC
Total Gate Charge (4.5V)			10		17	
Gate Source Charge	Q _{gs}			4.3		
Gate Drain Charge	Q _{gd}			4.7		
Turn-On DelayTime	t _{d(on)}			7		
Turn-On Rise Time	t _r	V _{GS} =10V, V _{DS} =18V, R _L =0.9Ω, R _{GEN} =3Ω		3.1		ns
Turn-Off DelayTime	t _{d(off)}			26		
Turn-Off Fall Time	t _f			4.5		
Body Diode Reverse Recovery Time	t _{rr}	I _F = 20A, dI/dt= 500A/us	13		21	
Body Diode Reverse Recovery Charge	Q _{rr}		30		47	nC
Maximum Body-Diode Continuous Current	I _S				5.5	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			1	V

Note : The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

■ Marking

Marking	4312 KC****
---------	----------------

N-Channel MOSFET

AO4312 (KO4312)

■ Typical Characteristics

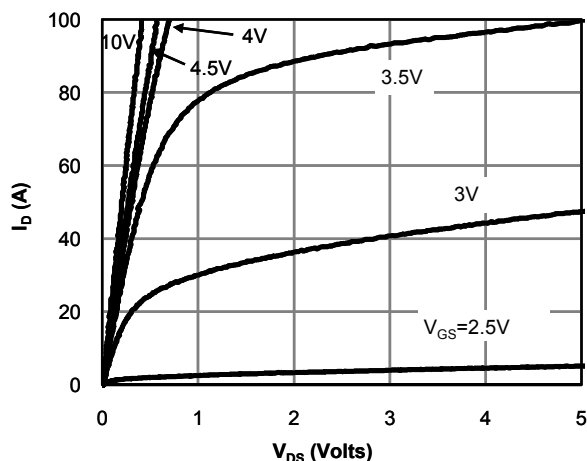


Fig 1: On-Region Characteristics (Note E)

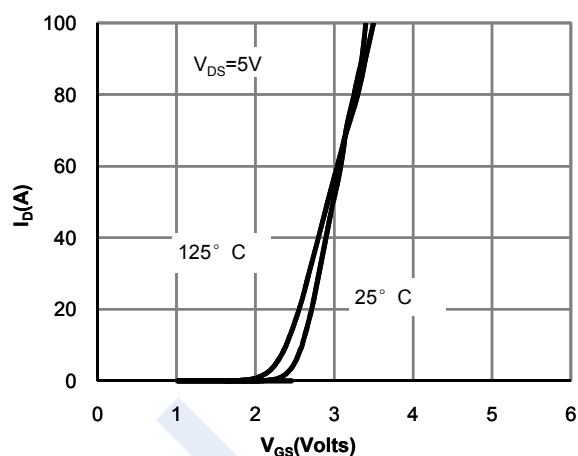


Figure 2: Transfer Characteristics (Note E)

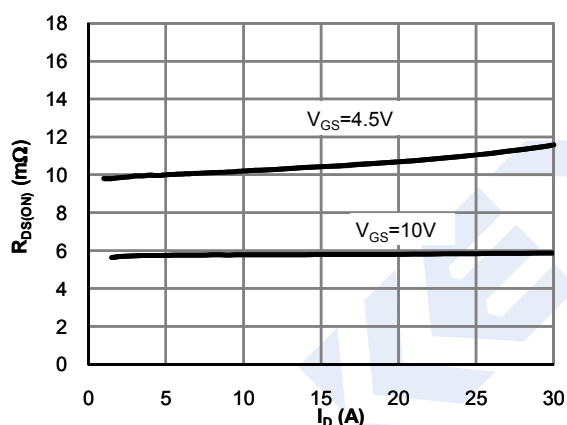


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

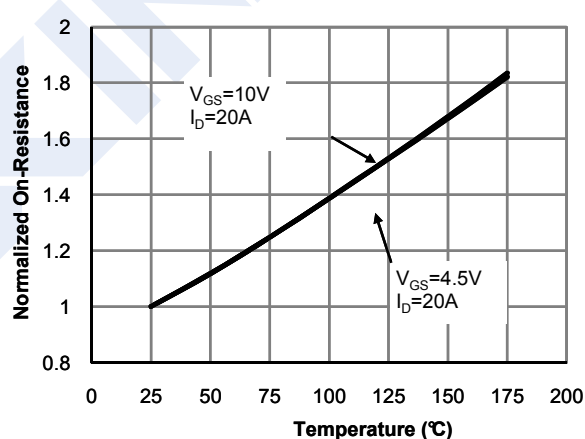


Figure 4: On-Resistance vs. Junction Temperature

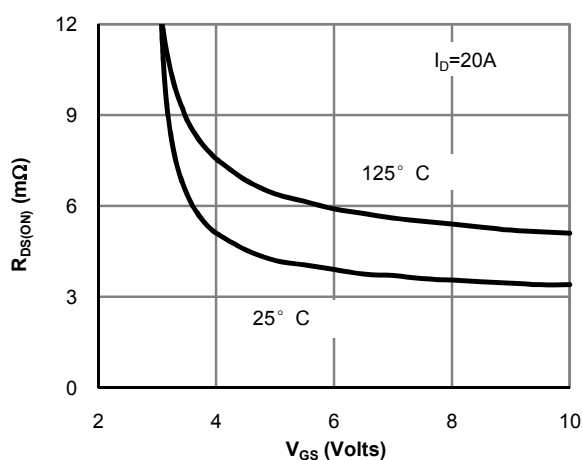


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

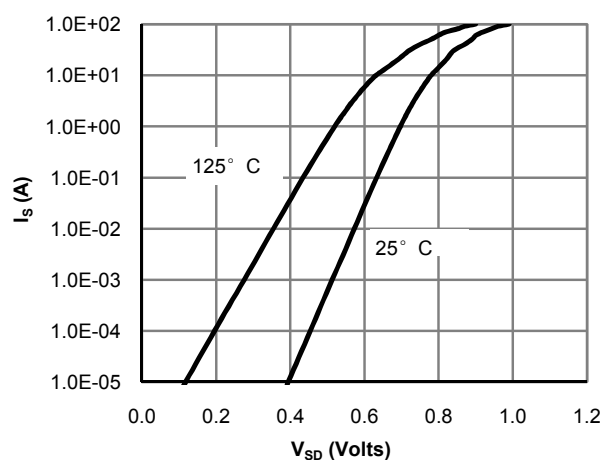


Figure 6: Body-Diode Characteristics (Note E)

N-Channel MOSFET

AO4312 (KO4312)

■ Typical Characteristics

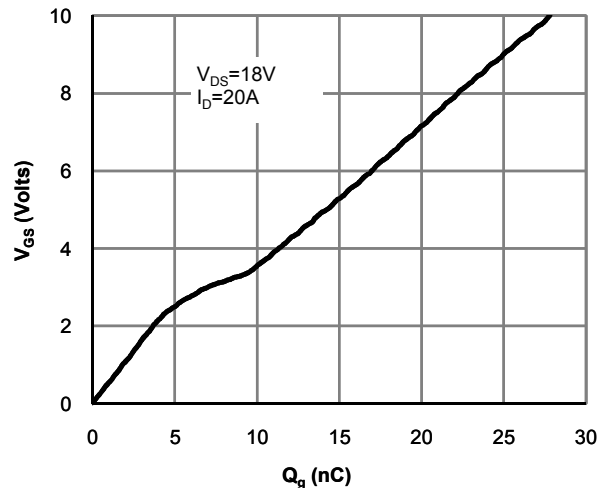


Figure 7: Gate-Charge Characteristics

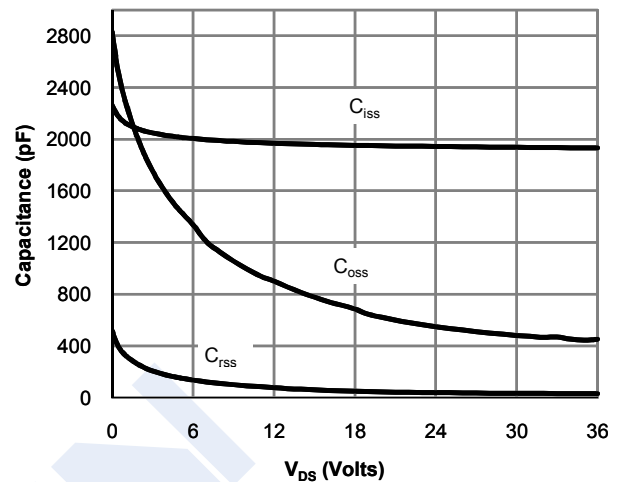


Figure 8: Capacitance Characteristics

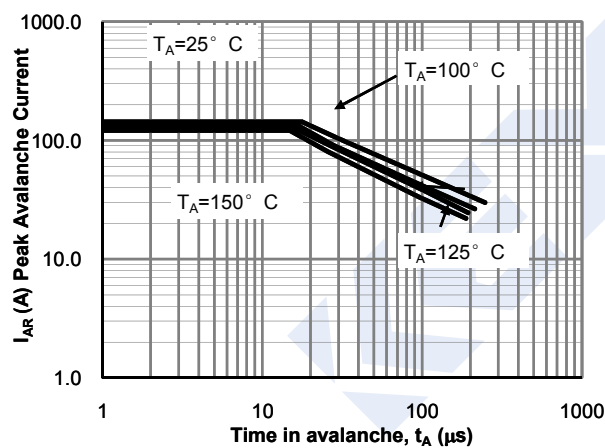


Figure 12: Single Pulse Avalanche capability (Note C)

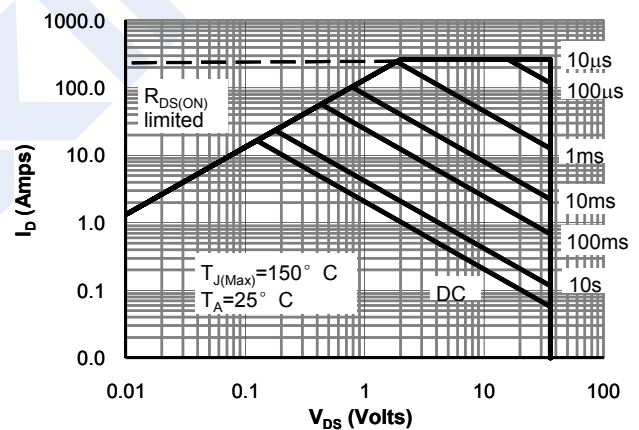


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

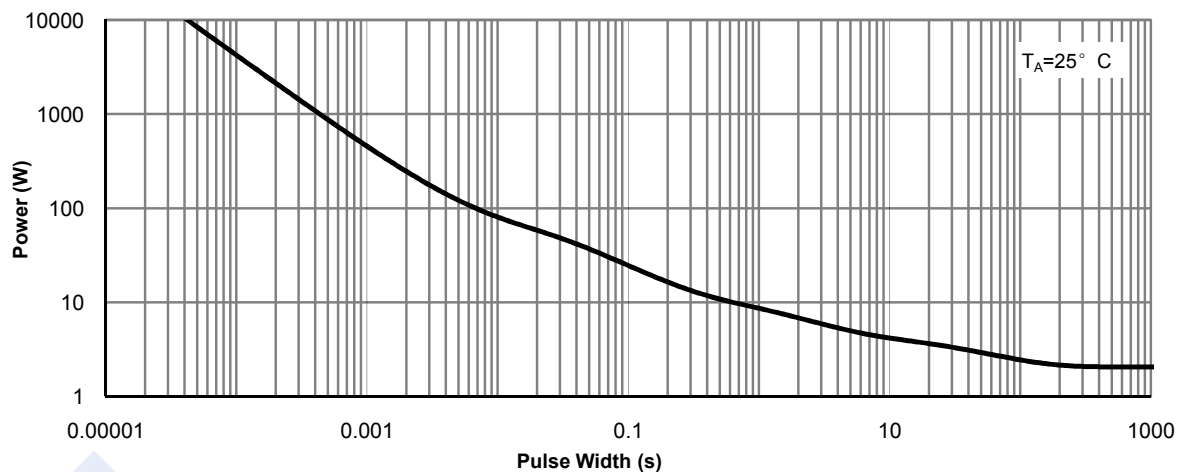


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

N-Channel MOSFET

AO4312 (KO4312)

■ Typical Characteristics

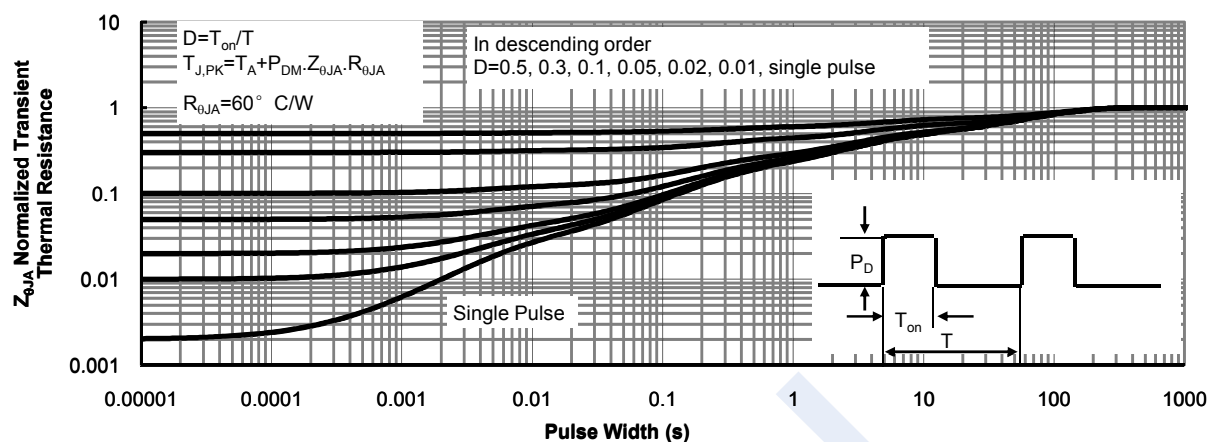


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)